



PTO/SB/08a/b (08-03)
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Substitute for form 1449A/B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)			Complete if Known		
			Application Number	10/602,720	
			Filing Date	June 25, 2003	
			First Named Inventor	John T. Moore	
			Art Unit	2811	
			Examiner Name	Not Yet Assigned	
Sheet	1	of	3	Attorney Docket Number	M4065.0675/P675

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
HL	A	US 2004/0035401	2/2004	Ramachandran et al.	
	B	US 2003/0212724	11/2003	Ovshinsky et al.	
	C	US 2003/0048744	3/2003	Ovshinsky et al.	
	D	US 2003/0212725	11/2003	Ovshinsky et al.	
	E	US RE 37,259E	7/2001	Ovshinsky	
	F	US 3,271,591	9/1966	Ovshinsky	
	G	US 3,961,314	6/1976	Klose et al.	
	H	US 3,966,317	6/1976	Wacks et al.	
	I	US 3,983,542	11/1976	Ovshinsky	
	J	US 3,988,720	10/1976	Ovshinsky	
	K	US 4,177,474	12/1979	Ovshinsky	
	L	US 4,267,261	5/1981	Hallman et al.	
	M	US 4,597,162	7/1986	Johnson et al.	
	N	US 4,608,296	8/1986	Keem et al.	
	O	US 4,637,895	1/1987	Ovshinsky et al.	
	P	US 4,646,266	2/1987	Ovshinsky et al.	
	Q	US 4,664,939	5/1987	Ovshinsky	
	R	US 4,668,968	5/1987	Ovshinsky et al.	
	S	US 4,670,763	6/1987	Ovshinsky et al.	
	T	US 4,673,957	6/1987	Ovshinsky et al.	
	U	US 4,678,679	7/1987	Ovshinsky	
	V	US 4,696,758	9/1987	Ovshinsky et al.	
	W	US 4,698,234	10/1987	Ovshinsky et al.	
	X	US 4,710,899	12/1987	Young et al.	
	Y	US 4,728,406	3/1988	Banerjee et al.	
	Z	US 4,737,379	4/1988	Hudgens et al.	
	A1	US 4,766,471	8/1988	Ovshinsky et al.	
	B1	US 4,769,338	9/1988	Ovshinsky et al.	
	C1	US 4,775,425	10/1988	Guha et al.	
	D1	US 4,788,594	11/1988	Ovshinsky et al.	
	E1	US 4,809,044	2/1989	Pryor et al.	
	F1	US 4,818,717	4/1989	Johnson et al.	
	G1	US 4,843,443	6/1989	Ovshinsky et al.	
	H1	US 4,845,533	7/1989	Pryor et al.	
	I1	US 4,853,785	8/1989	Ovshinsky et al.	
	J1	US 4,891,330	1/1990	Guha et al.	
	K1	US 5,128,099	7/1992	Strand et al.	
	L1	US 5,159,661	10/1992	Ovshinsky et al.	
	M1	US 5,166,758	11/1992	Ovshinsky et al.	
	N1	US 5,177,567	1/1993	Klersy et al.	
	O1	US 5,296,716	3/1994	Ovshinsky et al.	
	P1	US 5,335,219	8/1994	Ovshinsky et al.	
	Q1	US 5,359,205	10/1994	Ovshinsky	
	R1	US 5,341,328	8/1994	Ovshinsky et al.	
LM	S1	US 5,406,509	4/1995	Ovshinsky et al.	

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T1	US 5,414,271	5/1995	Ovshinsky et al.	
U1	US 5,534,711	7/1996	Ovshinsky et al.	
V1	US 5,534,712	7/1996	Ovshinsky et al.	
W1	US 5,536,947	7/1996	Klersy et al.	
X1	US 5,543,737	8/1996	Ovshinsky	
Y1	US 5,591,501	1/1997	Ovshinsky et al.	
Z1	US 5,596,522	1/1997	Ovshinsky et al.	
A2	US 5,687,112	11/1997	Ovshinsky	
B2	US 5,694,054	12/1997	Ovshinsky et al.	
C2	US 5,714,768	2/1998	Ovshinsky et al.	
D2	US 5,825,046	10/1998	Czubatyj et al.	
E2	US 5,912,839	6/1999	Ovshinsky et al.	
F2	US 5,933,365	8/1999	Klersy et al.	
G2	US 6,011,757	1/2000	Ovshinsky	
H2	US 6,087,674	7/2000	Ovshinsky et al.	
I2	US 6,141,241	10/2000	Ovshinsky et al.	
J2	US 6,339,544	1/2002	Chiang et al.	
K2	US 6,404,665	6/2002	Lowery et al.	
L2	US 6,429,064	8/2002	Wicker	
M2	US 6,437,383	8/2002	Xu	
N2	US 6,462,984	10/2002	Xu et al.	
O2	US 6,480,438	11/2002	Park	
P2	US 6,487,113	11/2002	Park et al.	
Q2	US 6,501,111	12/2002	Lowery	
R2	US 6,507,061	1/2003	Hudgens et al.	
S2	US 6,511,862	1/2003	Hudgens et al.	
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U2	US 6,512,241	1/2003	Lai	
V2	US 6,514,805	2/2003	Xu et al.	
W2	US 6,531,373	3/2003	Gill et al.	
X2	US 6,534,781	3/2003	Dennison	
Y2	US 6,545,287	4/2003	Chiang	
Z2	US 6,545,907	4/2003	Lowery et al.	
A3	US 6,555,860	4/2003	Lowery et al.	
B3	US 6,563,164	5/2003	Lowery et al.	
C3	US 6,566,700	5/2003	Xu	
D3	US 6,567,293	5/2003	Lowery et al.	
E3	US 6,569,705	5/2003	Chiang et al.	
F3	US 6,570,784	5/2003	Lowery	
G3	US 6,576,921	6/2003	Lowery	
H3	US 6,586,761	7/2003	Lowery	
I3	US 6,589,714	7/2003	Maimon et al.	
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L3	US 6,597,009	7/2003	Wicker	
M3	US 6,605,527	8/2003	Dennison et al.	
N3	US 6,613,604	9/2003	Maimon et al.	
O3	US 6,621,095	9/2003	Chiang et al.	
P3	US 6,625,054	9/2003	Lowery et al.	
Q3	US 6,642,102	11/2003	Xu	

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U1	R3	US 6,646,297	11/2003	Dennison	
	S3	US 6,649,928	11/2003	Dennison	
	T3	US 6,667,900	12/2003	Lowery et al.	
	U3	US 6,671,710	12/2003	Ovshinsky et al.	
	V3	US 6,673,648	1/2004	Lowrey	
	W3	US 6,673,700	1/2004	Dennison et al.	
	X3	US 6,674,115	1/2004	Hudgens et al.	
	Y3	US 6,687,427	2/2004	Ramalingam et al.	
	Z3	US 6,690,026	2/2004	Peterson	
	A4	US 6,696,355	2/2004	Dennison	
	B4	US 6,687,153	2/2004	Lowery	
	C4	US 6,707,712	3/2004	Lowery	
U1	D4	US 6,714,954	3/2004	Ovshinsky et al.	

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Examiner Initials*	Cite No. ¹	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	To
		Country Code ² -Number ³ -Kind Code ⁴ (if known)					

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¹ Applicant's unique citation designation number (optional). ² Applicant is to place a check mark here if English language Translation is attached.

Examiner Signature	Huan Hoang	Date Considered	8/18/04
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			Filing Date	June 25, 2003	
			First Named Inventor	John T. Moore	
			Art Unit	2811	
			Examiner Name	Not Yet Assigned	
Sheet	1	of	1	Attorney Docket Number	M4065.0675/P675

U.S. PATENT DOCUMENTS					
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		Number-Kind Code ² (if known)			

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)				

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NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
HH	AA	KAWAMOTO, Yoji And NISHIDA, Masaru, IONIC CONDUCTION IN As ₂ S ₃ -Ag ₂ S, GeS ₂ -GeS-Ag ₂ S AND P ₂ S ₅ -Ag ₂ S GLASSES, Journal of Non-Crystalline Solids 20 (1976) 393-404.	

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Huan Huang

8/18/04



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Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

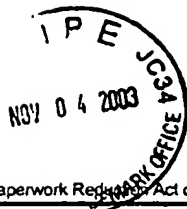
Sheet 1 of 11

Complete If Known

Application Number	10/602,720
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Examiner Name	N/A
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Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
HV	AA	2002/000666	1/3/2002	Kozicki et al.	
	AB	2002/0072188	6/13/2002	Gilton	
	AC	2002/0106849	08/08/2002	Moore	
	AD	2002/0123169	9/2002	Moore et al.	
	AE	2002/0123248	9/2002	Moore et al.	
	AF	2002/0160551	10/31/2002	Harshfield	
	AG	2002/0163828	11/07/2002	Krieger et al.	
	AH	2002/0168820	11/2002	Kozicki	
	AI	2002/0123169	09/05/2002	Moore et al.	
	AJ	2002/0123170	09/05/2002	Moore et al.	
	AK	2002/0123248	09/05/2002	Moore et al.	
	AL	2002/0127886	09/12/2002	Moore et al.	
	AM	2002/0132417	09/09/2002	Li	
	AN	2002/0168852	11/14/2002	Harshfield et al.	
	AO	2002/0190289	12/19/2002	Harshfield et al.	
	AP	2002/0190350	12/19/2002	Kozicki et al.	
	AQ	2003/0001229	01/02/2003	Moore et al.	
	AR	2003/0027416	02/06/2003	Moore	
	AS	2003/0032254	02/13/2003	Gilton	
	AT	2003/0035314	02/20/2003	Kozicki	
	AU	2003/0035315	02/20/2003	Kozicki	
	AV	2003/0038301	02/27/2003	Moore	
	AW	2003/0043631	03/06/2003	Gilton et al.	
	AX	2003/0045049	03/06/2003	Campbell et al.	
	AY	2003/0045054	03/06/2003	Campbell et al.	
	AZ	2003/0047765	03/13/2003	Campbell	
	AA1	2003/0047772	03/13/2003	Li	
	AB1	2003/0047773	03/13/2003	Li	
	AC1	2003/0048519	03/13/2003	Kozicki	
	AD1	2003/0049912	03/13/2003	Campbell et al.	
	AE1	2003/0068861	04/10/2003	Li	
	AF1	2003/0068862	04/10/2003	Li	
	AG1	2003/0095426	05/22/2003	Hush et al.	
	AH1	2003/0096497	05/22/2003	Moore et al.	
	AI1	2003/0107105	06/12/2003	Kozicki	
	AJ1	2003/0117831	06/26/2003	Hush	
	AK1	2003/0128612	07/10/2003	Moore et al.	
	AL1	2003/0137869	07/24/2003	Kozicki	
	AM1	2003/0143782	07/31/2003	Gilton et al.	
	AN1	2003/1055589	08/21/2003	Campbell et al.	
	AO1	2003/0155606	08/21/2003	Campbell et al.	
	AP1	2003/0156447	08/21/2003	Kozicki	
	AQ1	2003/0156463	08/21/2003	Casper et al.	
HV	AR1	3,622,319	11/1971	Sharp	



PTO/SB/08A (10-01)

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			Art Unit	N/A	
			Examiner Name	N/A	
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AS1	3,743,847	7/1973	Boland	
AT1	4,269,935	5/1981	Masters et al.	
AU1	4,312,938	1/1982	Drexler, et al.	
AV1	4,316,946	1/1982	Masters, et al.	
AW1	4,320,191	3/1982	Yoshikawa et al.	
AX1	4,405,710	9/1983	Balasubramanyam et al.	
AY1	4,419,421	12/1983	Wichelhaus, et al.	
AZ1	4,499,557	2/1985	Holmberg et al.	
AA2	4,671,618	06/09/1987	Wu et al.	
AB2	4,795,657	1/1989	Formigoni et al.	
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AE2	5,177,567	1/1993	Klersy et al.	
AF2	5,219,788	6/1993	Abernathy et al.	
AG2	5,238,862	8/1993	Blalock et al.	
AH2	5,272,359	12/21/1993	Nagasubramanian et al.	
AI2	5,314,772	5/24/1994	Kozicki	
AJ2	5,315,131	5/1994	Kishimoto et al.	
AK2	5,350,484	9/1994	Gardner et al.	
AL2	5,360,981	11/1994	Owen et al.	
AM2	5,500,532	3/19/1996	Kozicki et al.	
AN2	5,512,328	4/1996	Yoshimura et al.	
AO2	5,512,773	4/1996	Wolf et al.	
AP2	5,726,083	3/1998	Takaishi	
AQ2	5,751,012	5/12/1998	Wolstenholme et al.	
AR2	5,761,115	6/1998	Kozicki et al.	
AS2	5,789,277	8/1998	Zahorik et al.	
AT2	5,814,527	9/29/1998	Wolstenholme et al	
AU2	5,818,749	10/06/1998	Harshfield	
AV2	5,841,150	11/1998	Gonzalez et al.	
AW2	5,846,889	12/1998	Harbison et al.	
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AA3	5,914,893	6/22/1999	Kozicki et al.	
AB3	5,920,788	7/1999	Reinberg	
AC3	5,998,066	12/1999	Block et al.	
AD3	6,031,287	2/29/2000	Harshfield	
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AF3	6,077,729	6/2000	Harshfield	
AG3	6,084,796	7/4/2000	Kozicki et al.	
AH3	6,177,338	1/2001	Liaw et al.	
AI3	6,117,720	9/2000	Harshfield	
AJ3	6,143,604	11/2000	Chiang et al.	
AK3	6,236,059	5/2001	Wolsteinholme et al.	
AL3	6,297,170	10/2001	Gabriel et al.	
AM3	6,300,684	10/2001	Gonzalez et al.	
AN3	6,316,784	11/2001	Zahorik et al.	
AO3	6,329,606	12/2001	Freyman et al.	



PTO/SB/08A (10-01)

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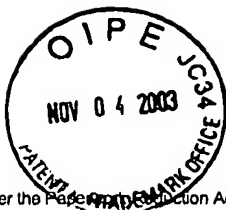
AP3	6,348,365	2/19/2002	Moore et al.	
AQ3	6,350,679	2/2002	McDaniel et al.	
AR3	6,376,284	4/2002	Gonzalez et al.	
AS3	6,388,324	5/14/2002	Kozicki et al.	
AT3	6,391,688	5/2002	Gonzalez et al.	
AU3	6,414,376	7/2002	Thakur et al.	
AV3	6,418,049	7/9/2002	Kozicki et al.	
AW3	6,420,725	7/16/2002	Harshfield	
AX3	6,423,628	7/2002	Li et al.	
AY3	6,440,837	8/27/2002	Harshfield	
AZ3	6,469,364	10/2002	Kozicki	
AA4	6,473,332	10/2002	Ignatiev et al.	
AB4	6,487,106	11/26/2002	Kozicki	
AC4	6,635,914	10/21/2003	Kozicki	

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		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)				
HK	BA	56126916	10/19981	Akira et al.		
I	BB	WO 97/48032	12/18/1997	Kozicki et al.		
	BC	WO 99/28914	06/10/1999	Kozicki et al.		
	BD	WO 00/48196	08/17/2000	Kozicki et al.		
HK	BE	WO 02/21542	03/14/2002	Kozicki et al.		

Examiner Signature	Huan Hoang	Date Considered	8/18/04
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			First Named Inventor	John T. Moore	
			Group Art Unit	N/A	
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			Examiner Name	N/A	
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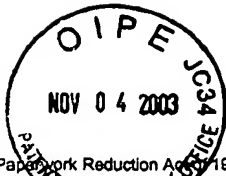


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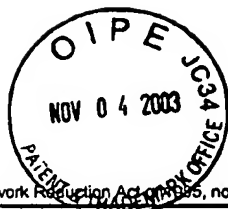
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Substitute for form 1449B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Complete if Known			
		Application Number	10/602,720		
		Filing Date	June 25, 2003		
		First Named Inventor	John T. Moore		
		Group Art Unit	N/A		
		Examiner Name	N/A		
Sheet	9	of	11	Attorney Docket Number	M4065.0675/P675

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Examiner Signature	Huan Huan	Date Considered	8/18/04
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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